

**Amended claims:**

- B<sup>1</sup>
1. (Amended) A device formed in a semiconductor material of a first conductivity type, the semiconductor material having a dopant concentration, the device comprising:  
a well of a second conductivity type formed in the semiconductor material, the well having a dopant concentration;  
a first region of the second conductivity type formed in the well, the first region having a dopant concentration greater than the dopant concentration of the well, the first region being connected to a first node;  
a second region of the first conductivity type formed in the well, the second region having a dopant concentration greater than the dopant concentration of the semiconductor material, the second region being connected to the first node;  
a third region of the second conductivity type formed in the semiconductor material, the third region having a dopant concentration greater than the dopant concentration of the well, the third region being connected to a second node, and  
a fourth region of the first conductivity type formed in the semiconductor material, the fourth region having a dopant concentration greater than the dopant concentration of the semiconductor material, the fourth region being connected to the second node, wherein the second region is reduced in size compared to a conventional LVTSCR of the same process.
- B<sup>2</sup>
3. (Amended) The device of claim 2, wherein the third region is increased in size relative to that of a conventional LVTSCR of the same process, to reduce space charge neutralization.
- B<sup>3</sup>
9. (Amended) A method of providing a device having a higher holding voltage than a LVTSCR and supporting a higher current than a GGNMOS, comprising providing a LVTSCR-like structure having a p+ emitter that is sufficiently reduced in size so as to increase the holding voltage to a desired level.
- B<sup>4</sup>
11. A method of creating an ESD protection structure having a higher holding voltage than a conventional LVTSCR, comprising  
providing a LVTSCR-like structure, and  
manipulating the size of the p+ emitter.
12. A method of claim 11, further comprising using TCAD simulations to determine a p+ emitter size corresponding to a desired holding voltage.
13. A method of creating an ESD protection structure that supports a higher current than a conventional GGNMOS device, comprising  
providing a LVTSCR-like structure, and  
manipulating the size of the p+ emitter.
14. A method of claim 13, further comprising using TCAD simulations to determine a p+ emitter size corresponding to a desired current.
15. A method of varying the holding voltage of a LVTSCR, comprising  
adjusting the size of the p+ emitter.
- 3.

16. ~~A method of claim 15, further comprising adjusting the size of the n+ emitter.~~
17. A method of adjusting the holding voltage of an ESD protection structure that includes a semiconductor material of a first conductivity type, the semiconductor material having a dopant concentration;  
a well of a second conductivity type formed in the semiconductor material, the well having a dopant concentration;  
a first region of the second conductivity type formed in the well, the first region having a dopant concentration greater than the dopant concentration of the well, the first region being connected to a first node;  
a second region of the first conductivity type formed in the well, the second region having a dopant concentration greater than the dopant concentration of the semiconductor material, the second region being connected to the first node;  
a third region of the second conductivity type formed in the semiconductor material, the third region having a dopant concentration greater than the dopant concentration of the well, the third region being connected to a second node, and  
a fourth region of the first conductivity type formed in the semiconductor material, the fourth region having a dopant concentration greater than the dopant concentration of the semiconductor material, the fourth region being connected to the second node, comprising,  
adjusting the size of the second region.
18. A method of claim 17, further comprising adjusting the size of the third region.

B4  
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